74HC4053; 74HCT4053

Triple 2-channel analog multiplexer/demultiplexer

Rev. 9 — 10 February 2016 **Product data sheet**

1. General description

The 74HC4053; 74HCT4053 is a triple single-pole double-throw analog switch (3x SPDT) suitable for use in analog or digital 2:1 multiplexer/demultiplexer applications. Each switch features a digital select input (Sn), two independent inputs/outputs (nY0 and nY1) and a common input/output (nZ). A digital enable input ($\overline{E}$) is common to all switches. When $\overline{E}$ is HIGH, the switches are turned off. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC}.

2. Features and benefits

- Wide analog input voltage range from –5 V to +5 V
- Complies with JEDEC standard no. 7A
- Low ON resistance:
  - 80 Ω (typical) at $V_{CC} – V_{EE}$ = 4.5 V
  - 70 Ω (typical) at $V_{CC} – V_{EE}$ = 6.0 V
  - 60 Ω (typical) at $V_{CC} – V_{EE}$ = 9.0 V
- Logic level translation: to enable 5 V logic to communicate with ±5 V analog signals
- Typical ‘break before make’ built-in
- ESD protection:
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
  - CDM JESD22-C101E exceeds 1000 V
- Multiple package options
- Specified from –40 °C to +85 °C and –40 °C to +125 °C

3. Applications

- Analog multiplexing and demultiplexing
- Digital multiplexing and demultiplexing
- Signal gating

4. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC4053D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT4053D				
74HC4053DB	–40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1
74HCT4053DB				
74HC4053PW	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74HCT4053PW				
74HC4053BQ	–40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 × 3.5 × 0.85 mm	SOT763-1
74HCT4053BQ				

5. Functional diagram

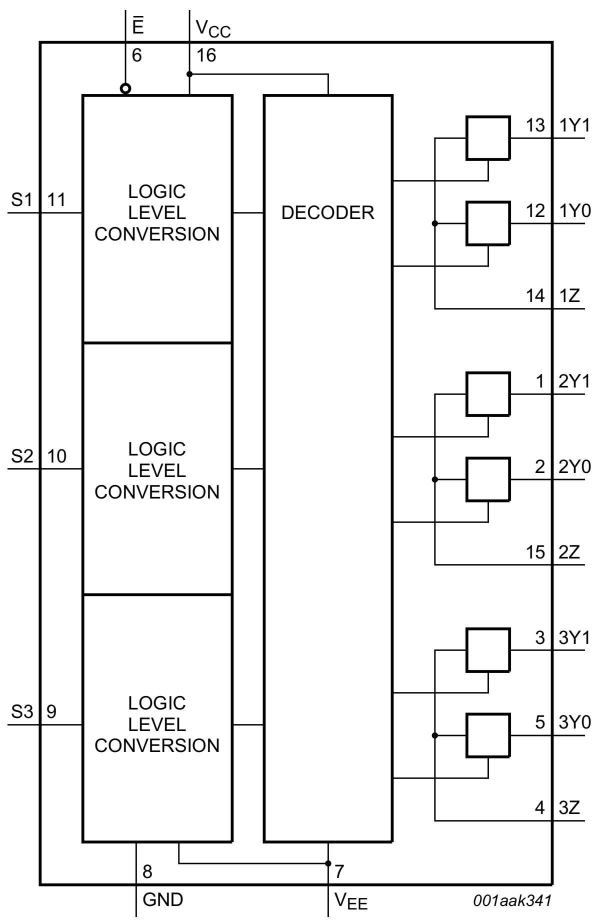

Fig 1. Functional diagram

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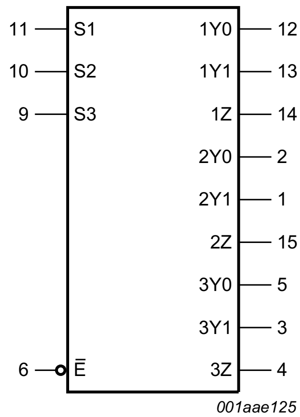

Fig 2. Logic symbol

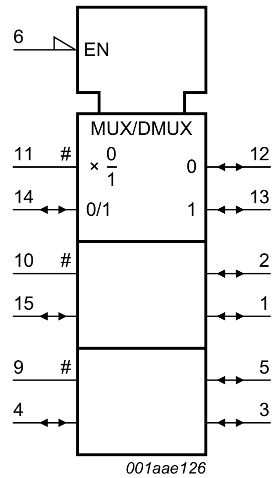

Fig 3. IEC logic symbol

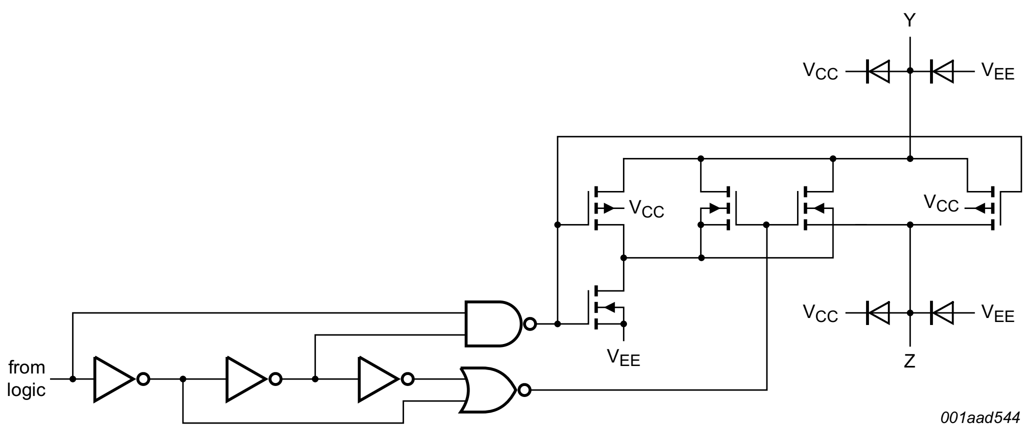

Fig 4. Schematic diagram (one switch)

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6. Pinning information

6.1 Pinning

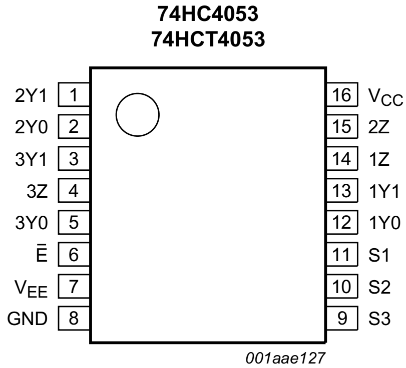
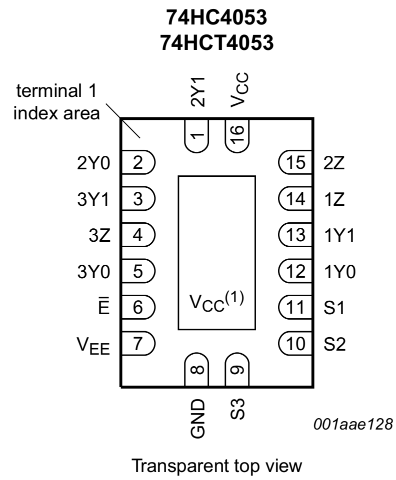


Fig 5. Pin configuration SO16, and (T)SSOP16



(1) This is not a supply pin. The substrate is attached to this pad using conductive die attach material. There is no electrical or mechanical requirement to solder this pad. However, if it is soldered, the solder land should remain floating or be connected to V_{CC}.

Fig 6. Pin configuration DHVQFN16

6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
$\overline{E}$	6	enable input (active LOW)
V_{EE}	7	supply voltage
GND	8	ground supply voltage
S1, S2, S3	11, 10, 9	select input
1Y0, 2Y0, 3Y0	12, 2, 5	independent input or output
1Y1, 2Y1, 3Y1	13, 1, 3	independent input or output
1Z, 2Z, 3Z	14, 15, 4	common output or input
V_{CC}	16	supply voltage

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7. Functional description

Table 3. Function table [1]

Inputs		Channel on
$\overline{E}$	Sn	
L	L	nY0 to nZ
L	H	nY1 to nZ
H	X	switches off

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to V_{SS} = 0 V (ground).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage		[1]	–0.5	+11.0	V
I_{IK}	input clamping current	V_I < –0.5 V or V_I > V_{CC} + 0.5 V		-	±20	mA
I_{SK}	switch clamping current	V_{SW} < –0.5 V or V_{SW} > V_{CC} + 0.5 V		-	±20	mA
I_{SW}	switch current	–0.5 V < V_{SW} < V_{CC} + 0.5 V		-	±25	mA
I_{EE}	supply current			-	±20	mA
I_{CC}	supply current			-	50	mA
I_{GND}	ground current			-	–50	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation	SO16, (T)SSOP16, and DHVQFN16 package	[2]	-	500	mW
P	power dissipation	per switch		-	100	mW

[1] To avoid drawing V_{CC} current out of terminal nZ, when switch current flows into terminals nYn, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminal nZ, no V_{CC} current will flow out of terminals nYn, and in this case there is no limit for the voltage drop across the switch, but the voltages at nYn and nZ may not exceed V_{CC} or V_{EE}.

[2] For SO16 packages: above 70 °C the value of P_{tot} derates linearly with 8 mW/K.
For SSOP16 and TSSOP16 packages: above 60 °C the value of P_{tot} derates linearly with 5.5 mW/K.
For DHVQFN16 packages: above 60 °C the value of P_{tot} derates linearly with 4.5 mW/K.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	74HC4053			74HCT4053			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage	see Figure 7 and Figure 8							
		V_{CC} – GND	2.0	5.0	10.0	4.5	5.0	5.5	V
		V_{CC} – V_{EE}	2.0	5.0	10.0	2.0	5.0	10.0	V
V_I	input voltage		GND	-	V_{CC}	GND	-	V_{CC}	V
V_{SW}	switch voltage		V_{EE}	-	V_{CC}	V_{EE}	-	V_{CC}	V

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Table 5. Recommended operating conditions *...continued*

Symbol	Parameter	Conditions	74HC4053			74HCT4053			Unit
			Min	Typ	Max	Min	Typ	Max	
T_{amb}	ambient temperature		–40	+25	+125	–40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V_{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V_{CC} = 6.0 V	-	-	83	-	-	-	ns/V
		V_{CC} = 10.0 V	-	-	31	-	-	-	ns/V

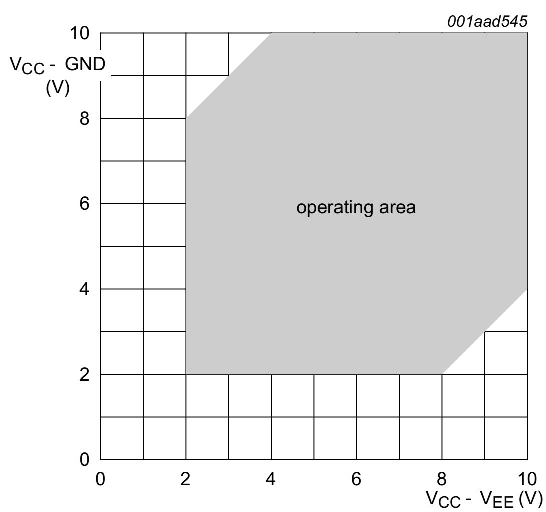

Fig 7. Guaranteed operating area as a function of the supply voltages for 74HC4053

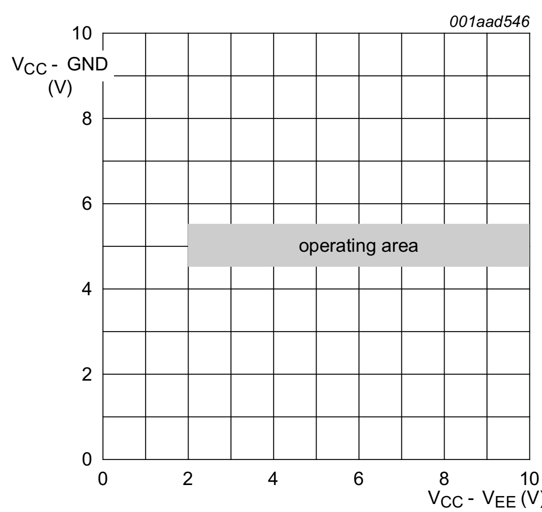

Fig 8. Guaranteed operating area as a function of the supply voltages for 74HCT4053

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10. Static characteristics

Table 6. R_{ON} resistance per switch for 74HC4053 and 74HCT4053

$V_I = V_{IH}$ or V_{IL}; for test circuit see Figure 9.
V_{is} is the input voltage at a nYn or nZ terminal, whichever is assigned as an input.
V_{os} is the output voltage at a nYn or nZ terminal, whichever is assigned as an output.
For 74HC4053: V_{CC} − GND or V_{CC} − V_{EE} = 2.0 V, 4.5 V, 6.0 V and 9.0 V.
For 74HCT4053: V_{CC} − GND = 4.5 V and 5.5 V, V_{CC} − V_{EE} = 2.0 V, 4.5 V, 6.0 V and 9.0 V.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
T_{amb} = 25 °C							
$R_{ON(peak)}$	ON resistance (peak)	$V_{is} = V_{CC}$ to V_{EE}					
		V_{CC} = 2.0 V; V_{EE} = 0 V; I_{SW} = 100 μA	[1]	-	-	-	Ω
		V_{CC} = 4.5 V; V_{EE} = 0 V; I_{SW} = 1000 μA		-	100	180	Ω
		V_{CC} = 6.0 V; V_{EE} = 0 V; I_{SW} = 1000 μA		-	90	160	Ω
		V_{CC} = 4.5 V; V_{EE} = −4.5 V; I_{SW} = 1000 μA		-	70	130	Ω
$R_{ON(rail)}$	ON resistance (rail)	$V_{is} = V_{EE}$					
		V_{CC} = 2.0 V; V_{EE} = 0 V; I_{SW} = 100 μA	[1]	-	150	-	Ω
		V_{CC} = 4.5 V; V_{EE} = 0 V; I_{SW} = 1000 μA		-	80	140	Ω
		V_{CC} = 6.0 V; V_{EE} = 0 V; I_{SW} = 1000 μA		-	70	120	Ω
		V_{CC} = 4.5 V; V_{EE} = −4.5 V; I_{SW} = 1000 μA		-	60	105	Ω
		$V_{is} = V_{CC}$					
		V_{CC} = 2.0 V; V_{EE} = 0 V; I_{SW} = 100 μA	[1]	-	150	-	Ω
		V_{CC} = 4.5 V; V_{EE} = 0 V; I_{SW} = 1000 μA		-	90	160	Ω
		V_{CC} = 6.0 V; V_{EE} = 0 V; I_{SW} = 1000 μA		-	80	140	Ω
		V_{CC} = 4.5 V; V_{EE} = −4.5 V; I_{SW} = 1000 μA		-	65	120	Ω
ΔR_{ON}	ON resistance mismatch between channels	$V_{is} = V_{CC}$ to V_{EE}					
		V_{CC} = 2.0 V; V_{EE} = 0 V	[1]	-	-	-	Ω
		V_{CC} = 4.5 V; V_{EE} = 0 V		-	9	-	Ω
		V_{CC} = 6.0 V; V_{EE} = 0 V		-	8	-	Ω
		V_{CC} = 4.5 V; V_{EE} = −4.5 V		-	6	-	Ω
T_{amb} = −40 °C to +85 °C							
$R_{ON(peak)}$	ON resistance (peak)	$V_{is} = V_{CC}$ to V_{EE}					
		V_{CC} = 2.0 V; V_{EE} = 0 V; I_{SW} = 100 μA	[1]	-	-	-	Ω
		V_{CC} = 4.5 V; V_{EE} = 0 V; I_{SW} = 1000 μA		-	-	225	Ω
		V_{CC} = 6.0 V; V_{EE} = 0 V; I_{SW} = 1000 μA		-	-	200	Ω
		V_{CC} = 4.5 V; V_{EE} = −4.5 V; I_{SW} = 1000 μA		-	-	165	Ω

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Table 6. R_{ON} resistance per switch for 74HC4053 and 74HCT4053 *…continued*
$V_I = V_{IH}$ or V_{IL}; for test circuit see Figure 9.
V_{is} is the input voltage at a nYn or nZ terminal, whichever is assigned as an input.
V_{os} is the output voltage at a nYn or nZ terminal, whichever is assigned as an output.
For 74HC4053: V_{CC} − GND or $V_{CC} - V_{EE}$ = 2.0 V, 4.5 V, 6.0 V and 9.0 V.
For 74HCT4053: V_{CC} − GND = 4.5 V and 5.5 V, $V_{CC} - V_{EE}$ = 2.0 V, 4.5 V, 6.0 V and 9.0 V.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{ON(rail)}$	ON resistance (rail)	$V_{is} = V_{EE}$				
		V_{CC} = 2.0 V; V_{EE} = 0 V; I_{SW} = 100 µA [1]	-	-	-	Ω
		V_{CC} = 4.5 V; V_{EE} = 0 V; I_{SW} = 1000 µA	-	-	175	Ω
		V_{CC} = 6.0 V; V_{EE} = 0 V; I_{SW} = 1000 µA	-	-	150	Ω
		V_{CC} = 4.5 V; V_{EE} = −4.5 V; I_{SW} = 1000 µA	-	-	130	Ω
		$V_{is} = V_{CC}$				
		V_{CC} = 2.0 V; V_{EE} = 0 V; I_{SW} = 100 µA [1]	-	-	-	Ω
		V_{CC} = 4.5 V; V_{EE} = 0 V; I_{SW} = 1000 µA	-	-	200	Ω
		V_{CC} = 6.0 V; V_{EE} = 0 V; I_{SW} = 1000 µA	-	-	175	Ω
		V_{CC} = 4.5 V; V_{EE} = −4.5 V; I_{SW} = 1000 µA	-	-	150	Ω
T_{amb} = −40 °C to +125 °C						
$R_{ON(peak)}$	ON resistance (peak)	$V_{is} = V_{CC}$ to V_{EE}				
		V_{CC} = 2.0 V; V_{EE} = 0 V; I_{SW} = 100 µA [1]	-	-	-	Ω
		V_{CC} = 4.5 V; V_{EE} = 0 V; I_{SW} = 1000 µA	-	-	270	Ω
		V_{CC} = 6.0 V; V_{EE} = 0 V; I_{SW} = 1000 µA	-	-	240	Ω
		V_{CC} = 4.5 V; V_{EE} = −4.5 V; I_{SW} = 1000 µA	-	-	195	Ω
$R_{ON(rail)}$	ON resistance (rail)	$V_{is} = V_{EE}$				
		V_{CC} = 2.0 V; V_{EE} = 0 V; I_{SW} = 100 µA [1]	-	-	-	Ω
		V_{CC} = 4.5 V; V_{EE} = 0 V; I_{SW} = 1000 µA	-	-	210	Ω
		V_{CC} = 6.0 V; V_{EE} = 0 V; I_{SW} = 1000 µA	-	-	180	Ω
		V_{CC} = 4.5 V; V_{EE} = −4.5 V; I_{SW} = 1000 µA	-	-	160	Ω
		$V_{is} = V_{CC}$				
		V_{CC} = 2.0 V; V_{EE} = 0 V; I_{SW} = 100 µA [1]	-	-	-	Ω
		V_{CC} = 4.5 V; V_{EE} = 0 V; I_{SW} = 1000 µA	-	-	240	Ω
		V_{CC} = 6.0 V; V_{EE} = 0 V; I_{SW} = 1000 µA	-	-	210	Ω
		V_{CC} = 4.5 V; V_{EE} = −4.5 V; I_{SW} = 1000 µA	-	-	180	Ω

[1] When supply voltages ($V_{CC} - V_{EE}$) near 2.0 V the analog switch ON resistance becomes extremely non-linear. When using a supply of 2 V, it is recommended to use these devices only for transmitting digital signals.

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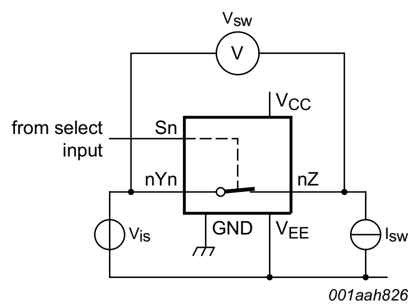
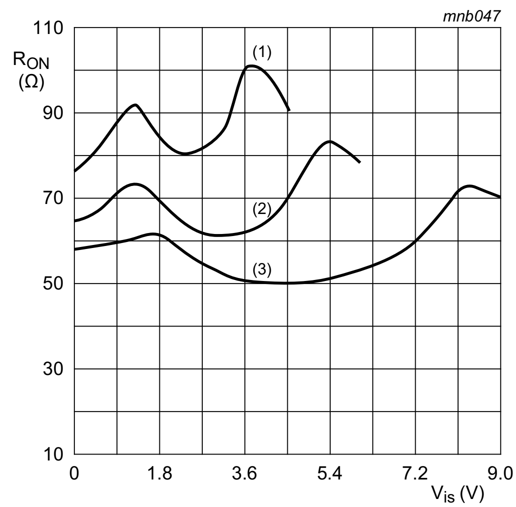


V_{is} = 0 V to ($V_{CC} - V_{EE}$).

$$R_{ON} = \frac{V_{sw}}{I_{sw}}$$

Fig 9. Test circuit for measuring R_{ON}



V_{is} = 0 V to ($V_{CC} - V_{EE}$).

(1) V_{CC} = 4.5 V

(2) V_{CC} = 6 V

(3) V_{CC} = 9 V

Fig 10. Typical R_{ON} as a function of input voltage V_{is}

Table 7. Static characteristics for 74HC4053

Voltages are referenced to GND (ground = 0 V).
V_{is} is the input voltage at pins nYn or nZ, whichever is assigned as an input.
V_{os} is the output voltage at pins nZ or nYn, whichever is assigned as an output.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	1.2	-	V
		V_{CC} = 4.5 V	3.15	2.4	-	V
		V_{CC} = 6.0 V	4.2	3.2	-	V
		V_{CC} = 9.0 V	6.3	4.7	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	0.8	0.5	V
		V_{CC} = 4.5 V	-	2.1	1.35	V
		V_{CC} = 6.0 V	-	2.8	1.8	V
		V_{CC} = 9.0 V	-	4.3	2.7	V
I_I	input leakage current	V_{EE} = 0 V; V_I = V_{CC} or GND				
		V_{CC} = 6.0 V	-	-	±0.1	μA
		V_{CC} = 10.0 V	-	-	±0.2	μA
$I_{S(OFF)}$	OFF-state leakage current	V_{CC} = 10.0 V; V_{EE} = 0 V; V_I = V_{IH} or V_{IL}; $\|V_{SW}\| = V_{CC} - V_{EE}$; see Figure 11				
		per channel	-	-	±0.1	μA
		all channels	-	-	±0.1	μA
$I_{S(ON)}$	ON-state leakage current	V_I = V_{IH} or V_{IL}; $\|V_{SW}\| = V_{CC} - V_{EE}$; V_{CC} = 10.0 V; V_{EE} = 0 V; see Figure 12	-	-	±0.1	μA

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Table 7. Static characteristics for 74HC4053 *...continued*
Voltages are referenced to GND (ground = 0 V).
V_{is} is the input voltage at pins nYn or nZ, whichever is assigned as an input.
V_{os} is the output voltage at pins nZ or nYn, whichever is assigned as an output.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CC}	supply current	V_{EE} = 0 V; V_I = V_{CC} or GND; V_{is} = V_{EE} or V_{CC}; V_{os} = V_{CC} or V_{EE}				
		V_{CC} = 6.0 V	-	-	8.0	μA
		V_{CC} = 10.0 V	-	-	16.0	μA
C_I	input capacitance		-	3.5	-	pF
C_{sw}	switch capacitance	independent pins nYn	-	5	-	pF
		common pins nZ	-	8	-	pF
T_{amb} = –40 °C to +85 °C						
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	-	-	V
		V_{CC} = 4.5 V	3.15	-	-	V
		V_{CC} = 6.0 V	4.2	-	-	V
		V_{CC} = 9.0 V	6.3	-	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	-	0.5	V
		V_{CC} = 4.5 V	-	-	1.35	V
		V_{CC} = 6.0 V	-	-	1.8	V
		V_{CC} = 9.0 V	-	-	2.7	V
I_I	input leakage current	V_{EE} = 0 V; V_I = V_{CC} or GND				
		V_{CC} = 6.0 V	-	-	±1.0	μA
		V_{CC} = 10.0 V	-	-	±2.0	μA
$I_{S(OFF)}$	OFF-state leakage current	V_{CC} = 10.0 V; V_{EE} = 0 V; V_I = V_{IH} or V_{IL}; $\lvert V_{SW}\rvert$ = V_{CC} – V_{EE}; see Figure 11				
		per channel	-	-	±1.0	μA
		all channels	-	-	±1.0	μA
$I_{S(ON)}$	ON-state leakage current	V_I = V_{IH} or V_{IL}; $\lvert V_{SW}\rvert$ = V_{CC} – V_{EE}; V_{CC} = 10.0 V; V_{EE} = 0 V; see Figure 12	-	-	±1.0	μA
I_{CC}	supply current	V_{EE} = 0 V; V_I = V_{CC} or GND; V_{is} = V_{EE} or V_{CC}; V_{os} = V_{CC} or V_{EE}				
		V_{CC} = 6.0 V	-	-	80.0	μA
		V_{CC} = 10.0 V	-	-	160.0	μA
T_{amb} = –40 °C to +125 °C						
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	-	-	V
		V_{CC} = 4.5 V	3.15	-	-	V
		V_{CC} = 6.0 V	4.2	-	-	V
		V_{CC} = 9.0 V	6.3	-	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	-	0.5	V
		V_{CC} = 4.5 V	-	-	1.35	V
		V_{CC} = 6.0 V	-	-	1.8	V
		V_{CC} = 9.0 V	-	-	2.7	V

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Table 7. Static characteristics for 74HC4053 *…continued*
Voltages are referenced to GND (ground = 0 V).
V_{is} is the input voltage at pins nYn or nZ, whichever is assigned as an input.
V_{os} is the output voltage at pins nZ or nYn, whichever is assigned as an output.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_I	input leakage current	V_{EE} = 0 V; V_I = V_{CC} or GND				
		V_{CC} = 6.0 V	-	-	±1.0	μA
		V_{CC} = 10.0 V	-	-	±2.0	μA
$I_{S(OFF)}$	OFF-state leakage current	V_{CC} = 10.0 V; V_{EE} = 0 V; V_I = V_{IH} or V_{IL}; $\|V_{SW}\|$ = V_{CC} − V_{EE}; see Figure 11				
		per channel	-	-	±1.0	μA
		all channels	-	-	±1.0	μA
$I_{S(ON)}$	ON-state leakage current	V_I = V_{IH} or V_{IL}; $\|V_{SW}\|$ = V_{CC} − V_{EE}; V_{CC} = 10.0 V; V_{EE} = 0 V; see Figure 12	-	-	±1.0	μA
I_{CC}	supply current	V_{EE} = 0 V; V_I = V_{CC} or GND; V_{is} = V_{EE} or V_{CC}; V_{os} = V_{CC} or V_{EE}				
		V_{CC} = 6.0 V	-	-	160.0	μA
		V_{CC} = 10.0 V	-	-	320.0	μA

Table 8. Static characteristics for 74HCT4053
Voltages are referenced to GND (ground = 0 V).
V_{is} is the input voltage at pins nYn or nZ, whichever is assigned as an input.
V_{os} is the output voltage at pins nZ or nYn, whichever is assigned as an output.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V_{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	V
I_I	input leakage current	V_I = V_{CC} or GND; V_{CC} = 5.5 V; V_{EE} = 0 V	-	-	±0.1	μA
$I_{S(OFF)}$	OFF-state leakage current	V_{CC} = 10.0 V; V_{EE} = 0 V; V_I = V_{IH} or V_{IL}; $\|V_{SW}\|$ = V_{CC} − V_{EE}; see Figure 11				
		per channel	-	-	±0.1	μA
		all channels	-	-	±0.1	μA
$I_{S(ON)}$	ON-state leakage current	V_{CC} = 10.0 V; V_{EE} = 0 V; V_I = V_{IH} or V_{IL}; $\|V_{SW}\|$ = V_{CC} − V_{EE}; see Figure 12	-	-	±0.1	μA
I_{CC}	supply current	V_I = V_{CC} or GND; V_{is} = V_{EE} or V_{CC}; V_{os} = V_{CC} or V_{EE}				
		V_{CC} = 5.5 V; V_{EE} = 0 V	-	-	8.0	μA
		V_{CC} = 5.0 V; V_{EE} = −5.0 V	-	-	16.0	μA
ΔI_{CC}	additional supply current	per input; V_I = V_{CC} − 2.1 V; other inputs at V_{CC} or GND; V_{CC} = 4.5 V to 5.5 V; V_{EE} = 0 V	-	50	180	μA
C_I	input capacitance		-	3.5	-	pF
C_{sw}	switch capacitance	independent pins nYn	-	5	-	pF
		common pins nZ	-	8	-	pF

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Table 8. Static characteristics for 74HCT4053 *...continued*

Voltages are referenced to GND (ground = 0 V).

V_{is} is the input voltage at pins nYn or nZ, whichever is assigned as an input.

V_{os} is the output voltage at pins nZ or nYn, whichever is assigned as an output.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = –40 °C to +85 °C						
V_{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	-	0.8	V
I_I	input leakage current	V_I = V_{CC} or GND; V_{CC} = 5.5 V; V_{EE} = 0 V	-	-	±1.0	μA
$I_{S(OFF)}$	OFF-state leakage current	V_{CC} = 10.0 V; V_{EE} = 0 V; V_I = V_{IH} or V_{IL}; $\|V_{SW}\|$ = V_{CC} – V_{EE}; see Figure 11				
		per channel	-	-	±1.0	μA
		all channels	-	-	±1.0	μA
$I_{S(ON)}$	ON-state leakage current	V_{CC} = 10.0 V; V_{EE} = 0 V; V_I = V_{IH} or V_{IL}; $\|V_{SW}\|$ = V_{CC} – V_{EE}; see Figure 12	-	-	±1.0	μA
I_{CC}	supply current	V_I = V_{CC} or GND; V_{is} = V_{EE} or V_{CC}; V_{os} = V_{CC} or V_{EE}				
		V_{CC} = 5.5 V; V_{EE} = 0 V	-	-	80.0	μA
		V_{CC} = 5.0 V; V_{EE} = –5.0 V	-	-	160.0	μA
ΔI_{CC}	additional supply current	per input; V_I = V_{CC} – 2.1 V; other inputs at V_{CC} or GND; V_{CC} = 4.5 V to 5.5 V; V_{EE} = 0 V	-	-	225	μA
T_{amb} = –40 °C to +125 °C						
V_{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	-	0.8	V
I_I	input leakage current	V_I = V_{CC} or GND; V_{CC} = 5.5 V; V_{EE} = 0 V	-	-	±1.0	μA
$I_{S(OFF)}$	OFF-state leakage current	V_{CC} = 10.0 V; V_{EE} = 0 V; V_I = V_{IH} or V_{IL}; $\|V_{SW}\|$ = V_{CC} – V_{EE}; see Figure 11				
		per channel	-	-	±1.0	μA
		all channels	-	-	±1.0	μA
$I_{S(ON)}$	ON-state leakage current	V_{CC} = 10.0 V; V_{EE} = 0 V; V_I = V_{IH} or V_{IL}; $\|V_{SW}\|$ = V_{CC} – V_{EE}; see Figure 12	-	-	±1.0	μA
I_{CC}	supply current	V_I = V_{CC} or GND; V_{is} = V_{EE} or V_{CC}; V_{os} = V_{CC} or V_{EE}				
		V_{CC} = 5.5 V; V_{EE} = 0 V	-	-	160.0	μA
		V_{CC} = 5.0 V; V_{EE} = –5.0 V	-	-	320.0	μA
ΔI_{CC}	additional supply current	per input; V_I = V_{CC} – 2.1 V; other inputs at V_{CC} or GND; V_{CC} = 4.5 V to 5.5 V; V_{EE} = 0 V	-	-	245	μA

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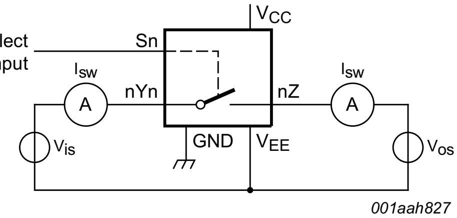
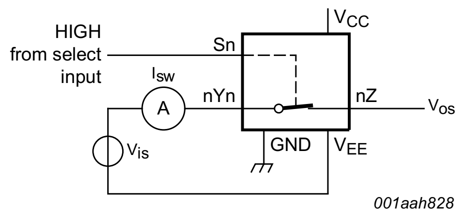


$V_{is} = V_{CC}$ and $V_{os} = V_{EE}$.

$V_{is} = V_{EE}$ and $V_{os} = V_{CC}$.

Fig 11. Test circuit for measuring OFF-state current



$V_{is} = V_{CC}$ and V_{os} = open-circuit.

$V_{is} = V_{EE}$ and V_{os} = open-circuit.

Fig 12. Test circuit for measuring ON-state current

11. Dynamic characteristics

Table 9. Dynamic characteristics for 74HC4053

GND = 0 V; $t_r = t_f$ = 6 ns; C_L = 50 pF; for test circuit see Figure 15.
V_{is} is the input voltage at a nYn or nZ terminal, whichever is assigned as an input.
V_{os} is the output voltage at a nYn or nZ terminal, whichever is assigned as an output.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
t_{pd}	propagation delay	V_{is} to V_{os}; $R_L = \infty\ \Omega$; see Figure 13 [1]				
		V_{CC} = 2.0 V; V_{EE} = 0 V	-	15	60	ns
		V_{CC} = 4.5 V; V_{EE} = 0 V	-	5	12	ns
		V_{CC} = 6.0 V; V_{EE} = 0 V	-	4	10	ns
		V_{CC} = 4.5 V; V_{EE} = −4.5 V	-	4	8	ns

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Table 9. Dynamic characteristics for 74HC4053 *...continued*

GND = 0 V; t_r = t_f = 6 ns; C_L = 50 pF; for test circuit see Figure 15.
V_{is} is the input voltage at a nYn or nZ terminal, whichever is assigned as an input.
V_{os} is the output voltage at a nYn or nZ terminal, whichever is assigned as an output.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
t_{on}	turn-on time	$\overline{E}$ to V_{os}; $R_L = \infty\ \Omega$; see Figure 14	[2]				
		V_{CC} = 2.0 V; V_{EE} = 0 V		-	60	220	ns
		V_{CC} = 4.5 V; V_{EE} = 0 V		-	20	44	ns
		V_{CC} = 5.0 V; V_{EE} = 0 V; C_L = 15 pF		-	17	-	ns
		V_{CC} = 6.0 V; V_{EE} = 0 V		-	16	37	ns
		V_{CC} = 4.5 V; V_{EE} = –4.5 V		-	15	31	ns
		Sn to V_{os}; $R_L = \infty\ \Omega$; see Figure 14	[2]				
		V_{CC} = 2.0 V; V_{EE} = 0 V		-	75	220	ns
		V_{CC} = 4.5 V; V_{EE} = 0 V		-	25	44	ns
		V_{CC} = 5.0 V; V_{EE} = 0 V; C_L = 15 pF		-	21	-	ns
		V_{CC} = 6.0 V; V_{EE} = 0 V		-	20	37	ns
		V_{CC} = 4.5 V; V_{EE} = –4.5 V		-	15	31	ns
t_{off}	turn-off time	$\overline{E}$ to V_{os}; R_L = 1 kΩ; see Figure 14	[3]				
		V_{CC} = 2.0 V; V_{EE} = 0 V		-	63	210	ns
		V_{CC} = 4.5 V; V_{EE} = 0 V		-	21	42	ns
		V_{CC} = 5.0 V; V_{EE} = 0 V; C_L = 15 pF		-	18	-	ns
		V_{CC} = 6.0 V; V_{EE} = 0 V		-	17	36	ns
		V_{CC} = 4.5 V; V_{EE} = –4.5 V		-	15	29	ns
		Sn to V_{os}; R_L = 1 kΩ; see Figure 14	[3]				
		V_{CC} = 2.0 V; V_{EE} = 0 V		-	60	210	ns
		V_{CC} = 4.5 V; V_{EE} = 0 V		-	20	42	ns
		V_{CC} = 5.0 V; V_{EE} = 0 V; C_L = 15 pF		-	17	-	ns
		V_{CC} = 6.0 V; V_{EE} = 0 V		-	16	36	ns
		V_{CC} = 4.5 V; V_{EE} = –4.5 V		-	15	29	ns
C_{PD}	power dissipation capacitance	per switch; V_I = GND to V_{CC}	[4]	-	36	-	pF
T_{amb} = –40 °C to +85 °C							
t_{pd}	propagation delay	V_{is} to V_{os}; $R_L = \infty\ \Omega$; see Figure 13	[1]				
		V_{CC} = 2.0 V; V_{EE} = 0 V		-	-	75	ns
		V_{CC} = 4.5 V; V_{EE} = 0 V		-	-	15	ns
		V_{CC} = 6.0 V; V_{EE} = 0 V		-	-	13	ns
		V_{CC} = 4.5 V; V_{EE} = –4.5 V		-	-	10	ns

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Table 9. Dynamic characteristics for 74HC4053 *...continued*

GND = 0 V; t_r = t_f = 6 ns; C_L = 50 pF; for test circuit see Figure 15.
V_{is} is the input voltage at a nYn or nZ terminal, whichever is assigned as an input.
V_{os} is the output voltage at a nYn or nZ terminal, whichever is assigned as an output.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
t_{on}	turn-on time	$\overline{E}$ to V_{os}; $R_L = \infty\ \Omega$; see Figure 14	[2]				
		V_{CC} = 2.0 V; V_{EE} = 0 V		-	-	275	ns
		V_{CC} = 4.5 V; V_{EE} = 0 V		-	-	55	ns
		V_{CC} = 6.0 V; V_{EE} = 0 V		-	-	47	ns
		V_{CC} = 4.5 V; V_{EE} = −4.5 V		-	-	39	ns
		Sn to V_{os}; $R_L = \infty\ \Omega$; see Figure 14	[2]				
		V_{CC} = 2.0 V; V_{EE} = 0 V		-	-	275	ns
		V_{CC} = 4.5 V; V_{EE} = 0 V		-	-	55	ns
		V_{CC} = 6.0 V; V_{EE} = 0 V		-	-	47	ns
		V_{CC} = 4.5 V; V_{EE} = −4.5 V		-	-	39	ns
t_{off}	turn-off time	$\overline{E}$ to V_{os}; R_L = 1 kΩ; see Figure 14	[3]				
		V_{CC} = 2.0 V; V_{EE} = 0 V		-	-	265	ns
		V_{CC} = 4.5 V; V_{EE} = 0 V		-	-	53	ns
		V_{CC} = 6.0 V; V_{EE} = 0 V		-	-	45	ns
		V_{CC} = 4.5 V; V_{EE} = −4.5 V		-	-	36	ns
		Sn to V_{os}; R_L = 1 kΩ; see Figure 14	[3]				
		V_{CC} = 2.0 V; V_{EE} = 0 V		-	-	265	ns
		V_{CC} = 4.5 V; V_{EE} = 0 V		-	-	53	ns
		V_{CC} = 6.0 V; V_{EE} = 0 V		-	-	45	ns
		V_{CC} = 4.5 V; V_{EE} = −4.5 V		-	-	36	ns
T_{amb} = −40 °C to +125 °C							
t_{pd}	propagation delay	V_{is} to V_{os}; $R_L = \infty\ \Omega$; see Figure 13	[1]				
		V_{CC} = 2.0 V; V_{EE} = 0 V		-	-	90	ns
		V_{CC} = 4.5 V; V_{EE} = 0 V		-	-	18	ns
		V_{CC} = 6.0 V; V_{EE} = 0 V		-	-	15	ns
		V_{CC} = 4.5 V; V_{EE} = −4.5 V		-	-	12	ns
t_{on}	turn-on time	$\overline{E}$ to V_{os}; $R_L = \infty\ \Omega$; see Figure 14	[2]				
		V_{CC} = 2.0 V; V_{EE} = 0 V		-	-	330	ns
		V_{CC} = 4.5 V; V_{EE} = 0 V		-	-	66	ns
		V_{CC} = 6.0 V; V_{EE} = 0 V		-	-	56	ns
		V_{CC} = 4.5 V; V_{EE} = −4.5 V		-	-	47	ns
		Sn to V_{os}; $R_L = \infty\ \Omega$; see Figure 14	[2]				
		V_{CC} = 2.0 V; V_{EE} = 0 V		-	-	330	ns
		V_{CC} = 4.5 V; V_{EE} = 0 V		-	-	66	ns
		V_{CC} = 6.0 V; V_{EE} = 0 V		-	-	56	ns
		V_{CC} = 4.5 V; V_{EE} = −4.5 V		-	-	47	ns

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Table 9. Dynamic characteristics for 74HC4053 *...continued*
GND = 0 V; t_r = t_f = 6 ns; C_L = 50 pF; for test circuit see Figure 15.
V_{is} is the input voltage at a nYn or nZ terminal, whichever is assigned as an input.
V_{os} is the output voltage at a nYn or nZ terminal, whichever is assigned as an output.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{off}	turn-off time	$\overline{E}$ to V_{os}; R_L = 1 kΩ; see Figure 14 [3]				
		V_{CC} = 2.0 V; V_{EE} = 0 V	-	-	315	ns
		V_{CC} = 4.5 V; V_{EE} = 0 V	-	-	63	ns
		V_{CC} = 6.0 V; V_{EE} = 0 V	-	-	54	ns
		V_{CC} = 4.5 V; V_{EE} = −4.5 V	-	-	44	ns
		Sn to V_{os}; R_L = 1 kΩ; see Figure 14 [3]				
		V_{CC} = 2.0 V; V_{EE} = 0 V	-	-	315	ns
		V_{CC} = 4.5 V; V_{EE} = 0 V	-	-	63	ns
		V_{CC} = 6.0 V; V_{EE} = 0 V	-	-	54	ns
		V_{CC} = 4.5 V; V_{EE} = −4.5 V	-	-	44	ns

[1] t_{pd} is the same as t_{PHL} and t_{PLH}.

[2] t_{on} is the same as t_{PZH} and t_{PZL}.

[3] t_{off} is the same as t_{PHZ} and t_{PLZ}.

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma\{(C_L + C_{sw}) \times V_{CC}^2 \times f_o\}$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
N = number of inputs switching;
$\Sigma\{(C_L + C_{sw}) \times V_{CC}^2 \times f_o\}$ = sum of outputs;
C_L = output load capacitance in pF;
C_{sw} = switch capacitance in pF;
V_{CC} = supply voltage in V.

Table 10. Dynamic characteristics for 74HCT4053
GND = 0 V; t_r = t_f = 6 ns; C_L = 50 pF; for test circuit see Figure 15.
V_{is} is the input voltage at a nYn or nZ terminal, whichever is assigned as an input.
V_{os} is the output voltage at a nYn or nZ terminal, whichever is assigned as an output.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
t_{pd}	propagation delay	V_{is} to V_{os}; R_L = ∞ Ω; see Figure 13 [1]				
		V_{CC} = 4.5 V; V_{EE} = 0 V	-	5	12	ns
		V_{CC} = 4.5 V; V_{EE} = −4.5 V	-	4	8	ns
t_{on}	turn-on time	$\overline{E}$ to V_{os}; R_L = 1 kΩ; see Figure 14 [2]				
		V_{CC} = 4.5 V; V_{EE} = 0 V	-	27	48	ns
		V_{CC} = 5.0 V; V_{EE} = 0 V; C_L = 15 pF	-	23	-	ns
		V_{CC} = 4.5 V; V_{EE} = −4.5 V	-	16	34	ns
		Sn to V_{os}; R_L = 1 kΩ; see Figure 14 [2]				
		V_{CC} = 4.5 V; V_{EE} = 0 V	-	25	48	ns
		V_{CC} = 5.0 V; V_{EE} = 0 V; C_L = 15 pF	-	21	-	ns
		V_{CC} = 4.5 V; V_{EE} = −4.5 V	-	16	34	ns

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Table 10. Dynamic characteristics for 74HCT4053 *...continued*

GND = 0 V; t_r = t_f = 6 ns; C_L = 50 pF; for test circuit see Figure 15.
V_{is} is the input voltage at a nYn or nZ terminal, whichever is assigned as an input.
V_{os} is the output voltage at a nYn or nZ terminal, whichever is assigned as an output.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
t_{off}	turn-off time	$\overline{E}$ to V_{os}; R_L = 1 kΩ; see Figure 14	[3]				
		V_{CC} = 4.5 V; V_{EE} = 0 V		-	24	44	ns
		V_{CC} = 5.0 V; V_{EE} = 0 V; C_L = 15 pF		-	20	-	ns
		V_{CC} = 4.5 V; V_{EE} = –4.5 V		-	15	31	ns
		Sn to V_{os}; R_L = 1 kΩ; see Figure 14	[3]				
		V_{CC} = 4.5 V; V_{EE} = 0 V		-	22	44	ns
		V_{CC} = 5.0 V; V_{EE} = 0 V; C_L = 15 pF		-	19	-	ns
		V_{CC} = 4.5 V; V_{EE} = –4.5 V		-	15	31	ns
C_{PD}	power dissipation capacitance	per switch; V_I = GND to V_{CC} − 1.5 V	[4]	-	36	-	pF
T_{amb} = –40 °C to +85 °C							
t_{pd}	propagation delay	V_{is} to V_{os}; R_L = ∞ Ω; see Figure 13	[1]				
		V_{CC} = 4.5 V; V_{EE} = 0 V		-	-	15	ns
		V_{CC} = 4.5 V; V_{EE} = –4.5 V		-	-	10	ns
t_{on}	turn-on time	$\overline{E}$ to V_{os}; R_L = 1 kΩ; see Figure 14	[2]				
		V_{CC} = 4.5 V; V_{EE} = 0 V		-	-	60	ns
		V_{CC} = 4.5 V; V_{EE} = –4.5 V		-	-	43	ns
		Sn to V_{os}; R_L = 1 kΩ; see Figure 14	[2]				
		V_{CC} = 4.5 V; V_{EE} = 0 V		-	-	60	ns
		V_{CC} = 4.5 V; V_{EE} = –4.5 V		-	-	43	ns
t_{off}	turn-off time	$\overline{E}$ to V_{os}; R_L = 1 kΩ; see Figure 14	[3]				
		V_{CC} = 4.5 V; V_{EE} = 0 V		-	-	55	ns
		V_{CC} = 4.5 V; V_{EE} = –4.5 V		-	-	39	ns
		Sn to V_{os}; R_L = 1 kΩ; see Figure 14	[3]				
		V_{CC} = 4.5 V; V_{EE} = 0 V		-	-	55	ns
		V_{CC} = 4.5 V; V_{EE} = –4.5 V		-	-	39	ns
T_{amb} = –40 °C to +125 °C							
t_{pd}	propagation delay	V_{is} to V_{os}; R_L = ∞ Ω; see Figure 13	[1]				
		V_{CC} = 4.5 V; V_{EE} = 0 V		-	-	18	ns
		V_{CC} = 4.5 V; V_{EE} = –4.5 V		-	-	12	ns
t_{on}	turn-on time	$\overline{E}$ to V_{os}; R_L = 1 kΩ; see Figure 14	[2]				
		V_{CC} = 4.5 V; V_{EE} = 0 V		-	-	72	ns
		V_{CC} = 4.5 V; V_{EE} = –4.5 V		-	-	51	ns
		Sn to V_{os}; R_L = 1 kΩ; see Figure 14	[2]				
		V_{CC} = 4.5 V; V_{EE} = 0 V		-	-	72	ns
		V_{CC} = 4.5 V; V_{EE} = –4.5 V		-	-	51	ns

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Table 10. Dynamic characteristics for 74HCT4053 *...continued*

GND = 0 V; t_r = t_f = 6 ns; C_L = 50 pF; for test circuit see Figure 15.

V_{is} is the input voltage at a nYn or nZ terminal, whichever is assigned as an input.

V_{os} is the output voltage at a nYn or nZ terminal, whichever is assigned as an output.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{off}	turn-off time	$\overline{E}$ to V_{os}; R_L = 1 kΩ; see Figure 14 [3]				
		V_{CC} = 4.5 V; V_{EE} = 0 V	-	-	66	ns
		V_{CC} = 4.5 V; V_{EE} = −4.5 V	-	-	47	ns
		Sn to V_{os}; R_L = 1 kΩ; see Figure 14 [3]				
		V_{CC} = 4.5 V; V_{EE} = 0 V	-	-	66	ns
		V_{CC} = 4.5 V; V_{EE} = −4.5 V	-	-	47	ns

[1] t_{pd} is the same as t_{PHL} and t_{PLH}.

[2] t_{on} is the same as t_{PZH} and t_{PZL}.

[3] t_{off} is the same as t_{PHZ} and t_{PLZ}.

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma\{(C_L + C_{sw}) \times V_{CC}^2 \times f_o\}$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

N = number of inputs switching;

$\Sigma\{(C_L + C_{sw}) \times V_{CC}^2 \times f_o\}$ = sum of outputs;

C_L = output load capacitance in pF;

C_{sw} = switch capacitance in pF;

V_{CC} = supply voltage in V.

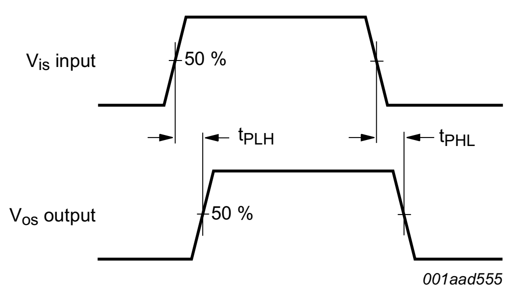

Fig 13. Input (V_{is}) to output (V_{os}) propagation delays

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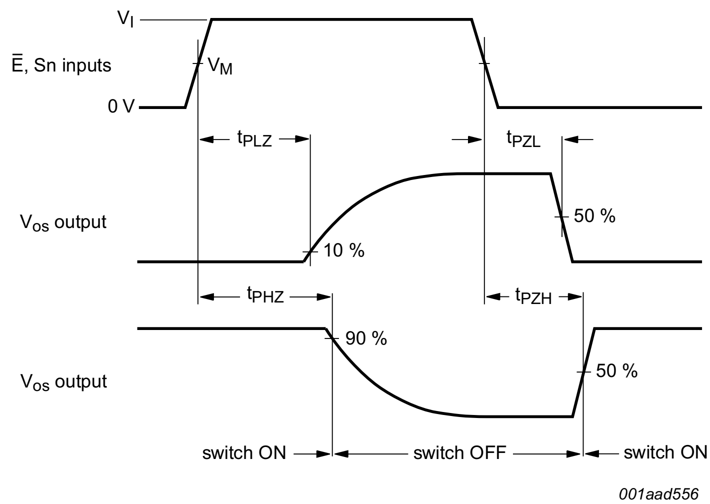
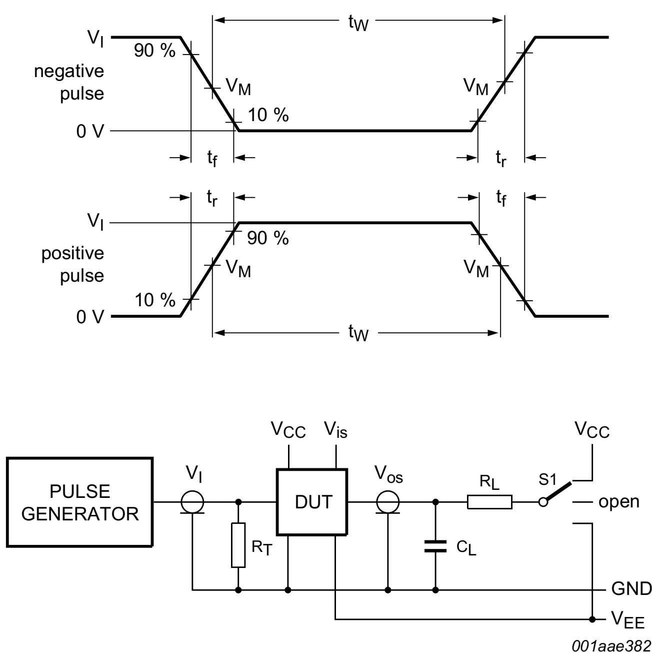


For 74HC4053: $V_M = 0.5 \times V_{CC}$.

For 74HCT4053: $V_M = 1.3$ V.

Fig 14. Turn-on and turn-off times



Definitions for test circuit; see Table 11:

R_T = termination resistance should be equal to the output impedance Z_o of the pulse generator.

C_L = load capacitance including jig and probe capacitance.

R_L = load resistance.

S1 = Test selection switch.

Fig 15. Test circuit for measuring AC performance

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Table 11. Test data

Test	Input				Load		S1 position
	V_I	V_{is}	t_r, t_f		C_L	R_L	
			at f_{max}	other[1]			
t_{PHL}, t_{PLH}	[2]	pulse	< 2 ns	6 ns	50 pF	1 kΩ	open
t_{PZH}, t_{PHZ}	[2]	V_{CC}	< 2 ns	6 ns	50 pF	1 kΩ	V_{EE}
t_{PZL}, t_{PLZ}	[2]	V_{EE}	< 2 ns	6 ns	50 pF	1 kΩ	V_{CC}

[1] $t_r = t_f$ = 6 ns; when measuring f_{max}, there is no constraint to t_r and t_f with 50 % duty factor.

[2] V_I values:

a) For 74HC4053: $V_I = V_{CC}$

b) For 74HCT4053: V_I = 3 V

11.1 Additional dynamic characteristics

Table 12. Additional dynamic characteristics

Recommended conditions and typical values; GND = 0 V; T_{amb} = 25 °C; C_L = 50 pF.
V_{is} is the input voltage at pins nYn or nZ, whichever is assigned as an input.
V_{os} is the output voltage at pins nYn or nZ, whichever is assigned as an output.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
d_{sin}	sine-wave distortion	f_i = 1 kHz; R_L = 10 kΩ; see Figure 16					
		V_{is} = 4.0 V (p-p); V_{CC} = 2.25 V; V_{EE} = −2.25 V		-	0.04	-	%
		V_{is} = 8.0 V (p-p); V_{CC} = 4.5 V; V_{EE} = −4.5 V		-	0.02	-	%
		f_i = 10 kHz; R_L = 10 kΩ; see Figure 16					
		V_{is} = 4.0 V (p-p); V_{CC} = 2.25 V; V_{EE} = −2.25 V		-	0.12	-	%
		V_{is} = 8.0 V (p-p); V_{CC} = 4.5 V; V_{EE} = −4.5 V		-	0.06	-	%
α_{iso}	isolation (OFF-state)	R_L = 600 Ω; f_i = 1 MHz; see Figure 17					
		V_{CC} = 2.25 V; V_{EE} = −2.25 V	[1]	-	−50	-	dB
		V_{CC} = 4.5 V; V_{EE} = −4.5 V	[1]	-	−50	-	dB
Xtalk	crosstalk	between two switches/multiplexers; R_L = 600 Ω; f_i = 1 MHz; see Figure 18					
		V_{CC} = 2.25 V; V_{EE} = −2.25 V	[1]	-	−60	-	dB
		V_{CC} = 4.5 V; V_{EE} = −4.5 V	[1]	-	−60	-	dB
V_{ct}	crosstalk voltage	peak-to-peak value; between control and any switch; R_L = 600 Ω; f_i = 1 MHz; $\overline{E}$ or Sn square wave between V_{CC} and GND; $t_r = t_f$ = 6 ns; see Figure 19					
		V_{CC} = 4.5 V; V_{EE} = 0 V		-	110	-	mV
		V_{CC} = 4.5 V; V_{EE} = −4.5 V		-	220	-	mV
$f_{(-3dB)}$	−3 dB frequency response	R_L = 50 Ω; see Figure 20					
		V_{CC} = 2.25 V; V_{EE} = −2.25 V	[2]	-	160	-	MHz
		V_{CC} = 4.5 V; V_{EE} = −4.5 V	[2]	-	170	-	MHz

[1] Adjust input voltage V_{is} to 0 dBm level (0 dBm = 1 mW into 600 Ω).

[2] Adjust input voltage V_{is} to 0 dBm level at V_{os} for 1 MHz (0 dBm = 1 mW into 50 Ω).

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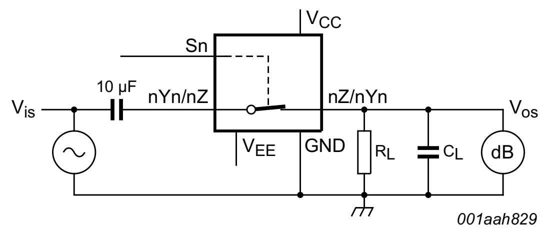
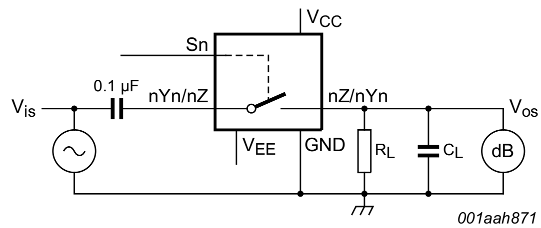
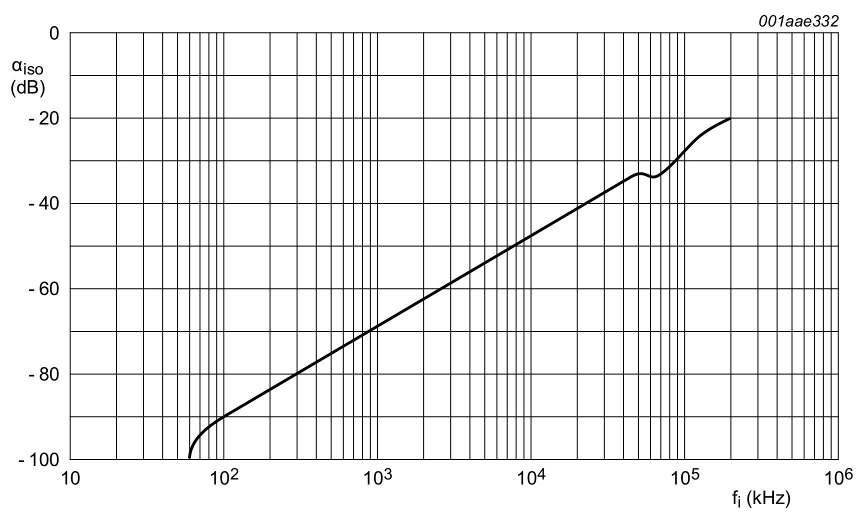


Fig 16. Test circuit for measuring sine-wave distortion



V_{CC} = 4.5 V; GND = 0 V; V_{EE} = –4.5 V; R_L = 600 Ω; R_S = 1 kΩ.

a. Test circuit



b. Isolation (OFF-state) as a function of frequency

Fig 17. Test circuit for measuring isolation (OFF-state)

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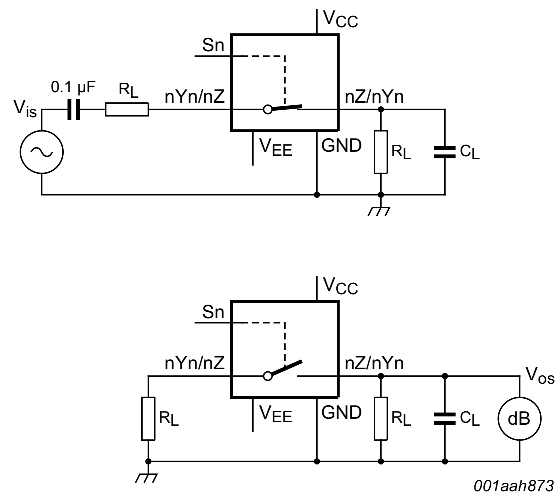

Fig 18. Test circuits for measuring crosstalk between any two switches/multiplexers

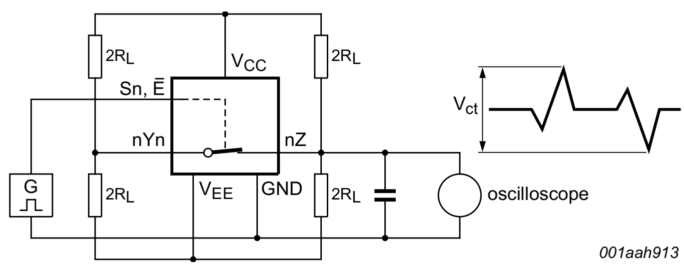

Fig 19. Test circuit for measuring crosstalk between control input and any switch

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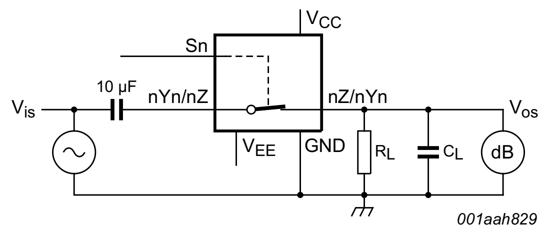
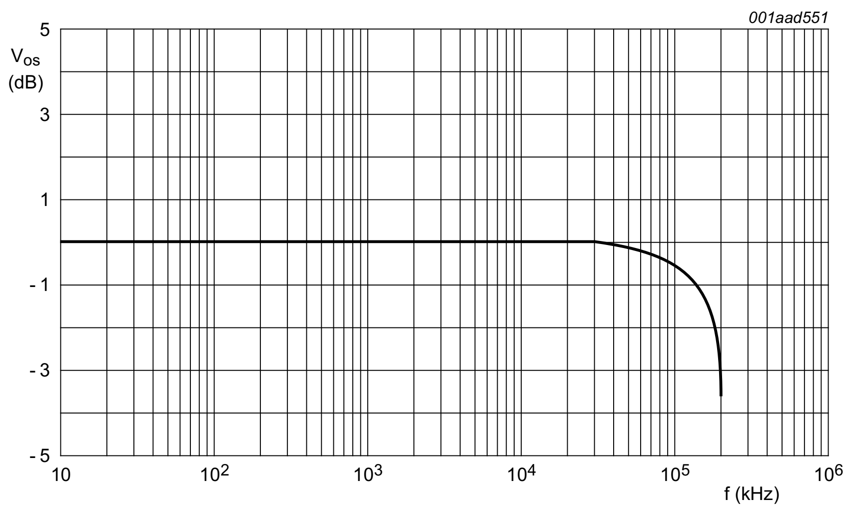


V_{CC} = 4.5 V; GND = 0 V; V_{EE} = −4.5 V; R_L = 50 Ω; R_S = 1 kΩ.

a. Test circuit



b. Typical frequency response

Fig 20. Test circuit for frequency response

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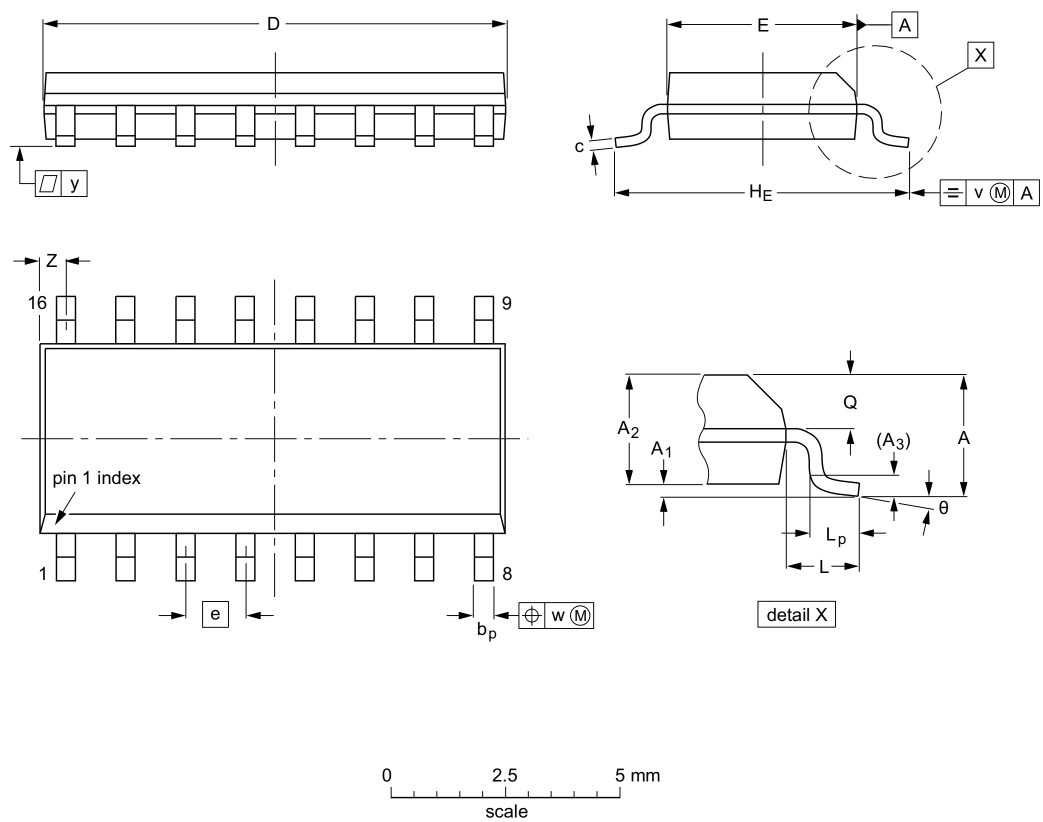
12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm **SOT109-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8° 0°
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT109-1	076E07	MS-012				~~99-12-27~~ 03-02-19

Fig 21. Package outline SOT109-1 (SO16)

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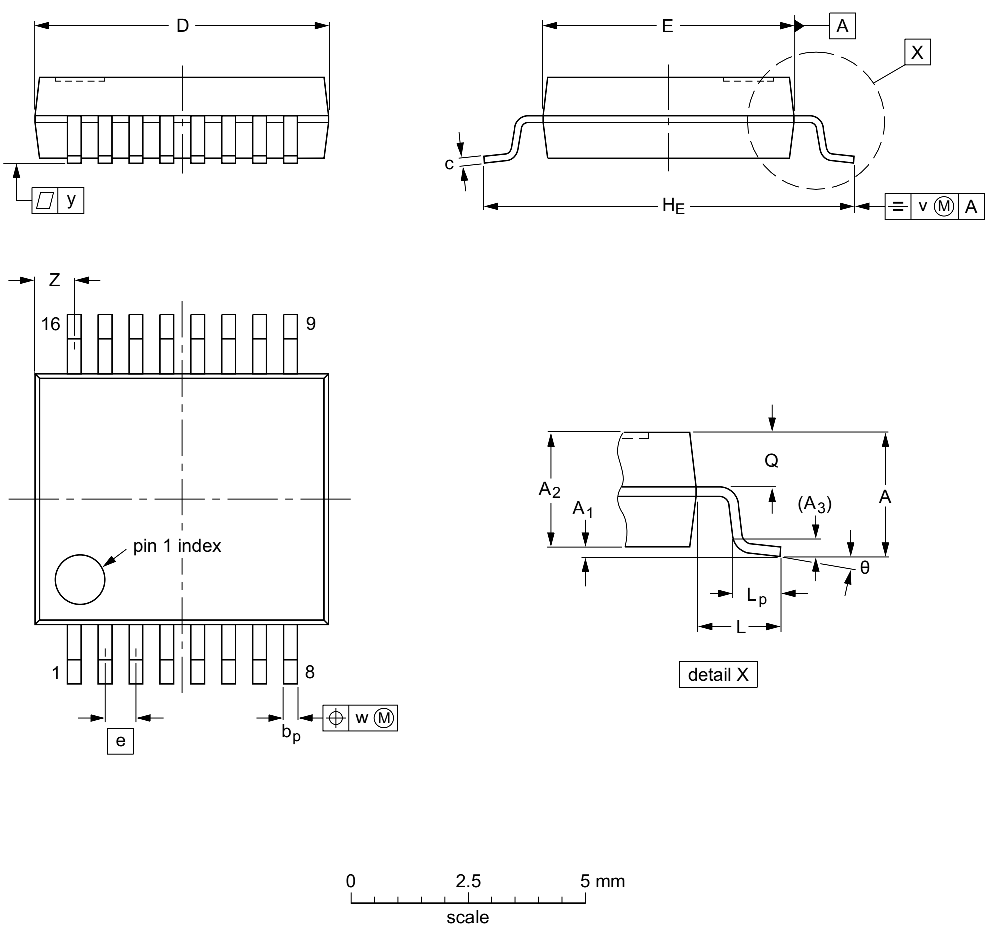
SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm **SOT338-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (1)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.00 0.55	8° 0°

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

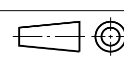
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT338-1		MO-150				~~99-12-27~~ 03-02-19

Fig 22. Package outline SOT338-1 (SSOP16)

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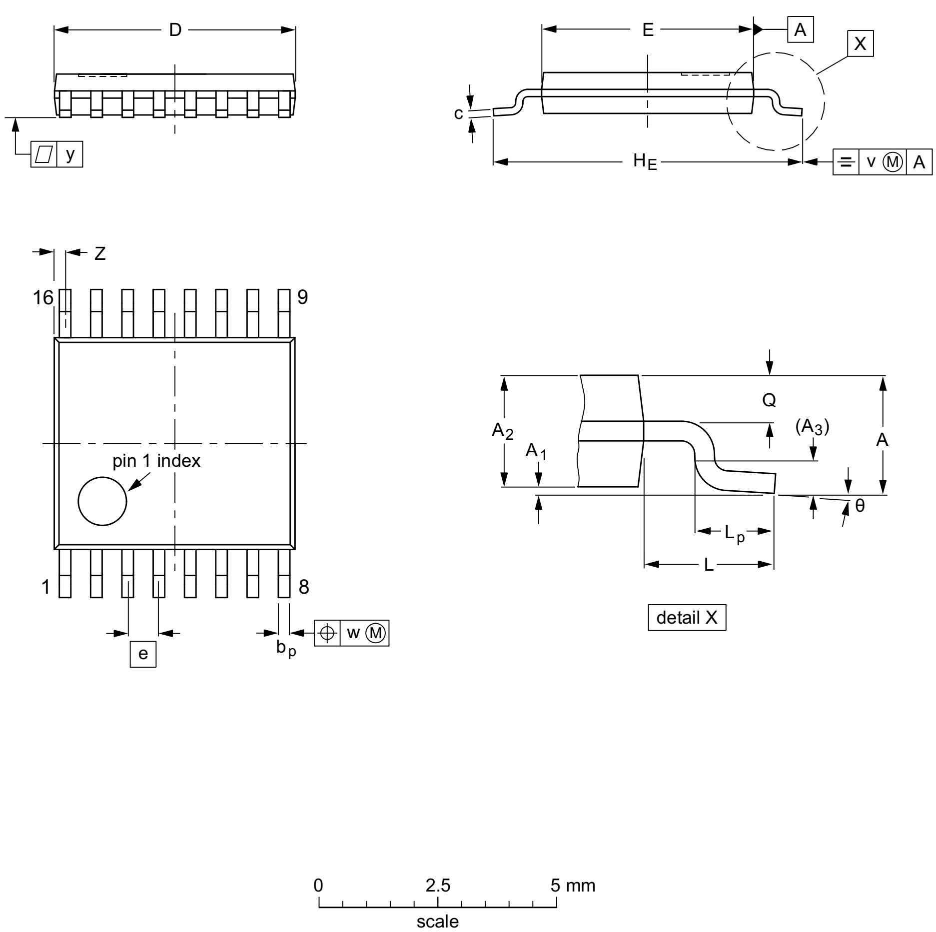
TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm **SOT403-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT403-1		MO-153				~~99-12-27~~ 03-02-18

Fig 23. Package outline SOT403-1 (TSSOP16)

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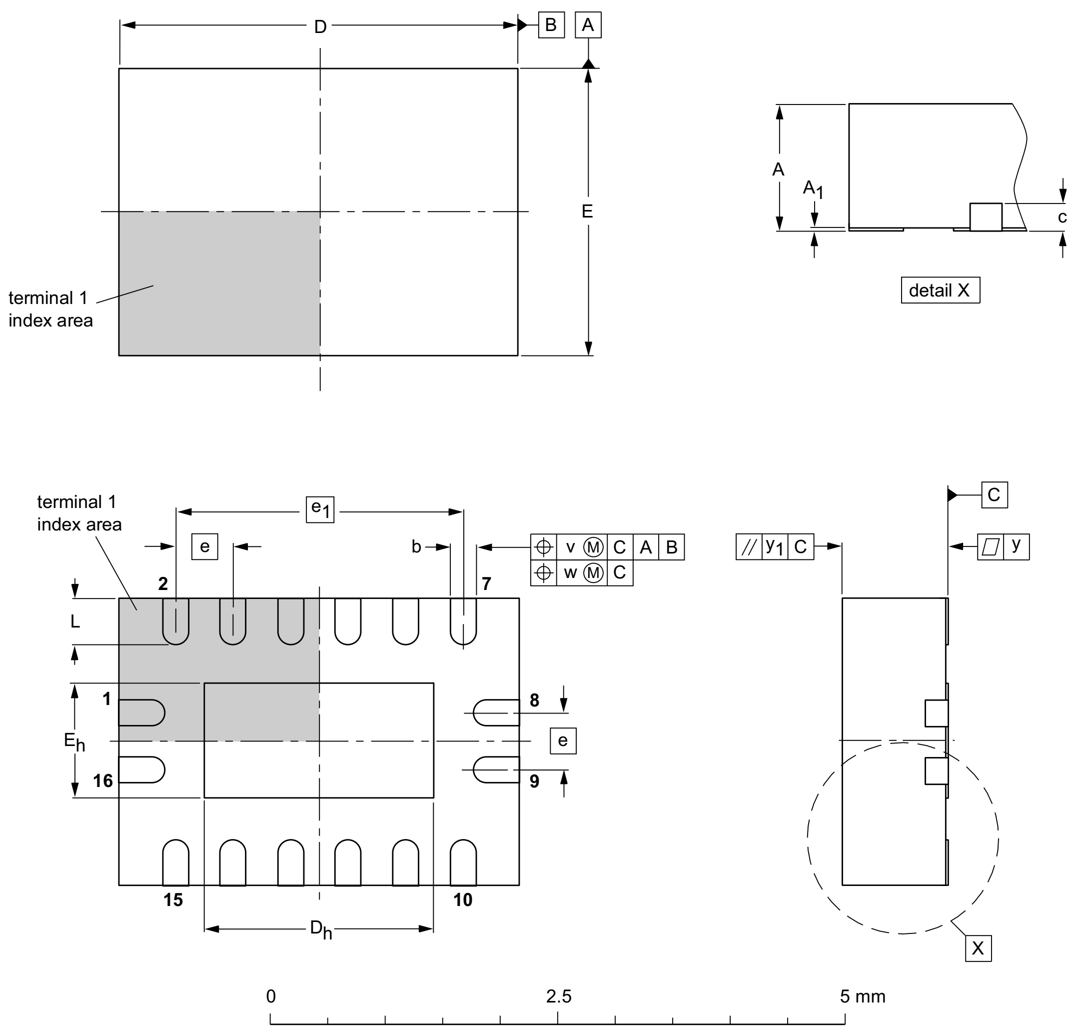
DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm **SOT763-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A(1) max.	A_1	b	c	D(1)	D_h	E(1)	E_h	e	e_1	L	v	w	y	y_1
mm	1	0.05 0.00	0.30 0.18	0.2	3.6 3.4	2.15 1.85	2.6 2.4	1.15 0.85	0.5	2.5	0.5 0.3	0.1	0.05	0.05	0.1

Note

1. Plastic or metal protrusions of 0.075 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT763-1	- - -	MO-241	- - -			~~02-10-17~~ 03-01-27

Fig 24. Package outline SOT763-1 (DHVQFN16)

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13. Abbreviations

Table 13. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

14. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT4053 v.9	20160210	Product data sheet	-	74HC_HCT4053 v.8
Modifications:	• Type numbers 74HC4053N and 74HCT4053N (SOT38-4) removed.			
74HC_HCT4053 v.8	20120719	Product data sheet	-	74HC_HCT4053 v.7
Modifications:	• CDM added to features.			
74HC_HCT4053 v.7	20111213	Product data sheet	-	74HC_HCT4053 v.6
Modifications:	• Legal pages updated.			
74HC_HCT4053 v.6	20110511	Product data sheet	-	74HC_HCT4053 v.5
74HC_HCT4053 v.5	20110118	Product data sheet	-	74HC_HCT4053 v.4
74HC_HCT4053 v.4	20060509	Product data sheet	-	74HC_HCT4053 v.3
74HC_HCT4053 v.3	20060315	Product data sheet	-	74HC_HCT4053_CNV v.2
74HC_HCT4053_CNV v.2	19901201	Product specification	-	-

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Date of release: 10 February 2016
Document identifier: 74HC_HCT4053